

STTH302

HIGH EFFICIENCY ULTRAFAST DIODE

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	3A
V _{RRM}	200 V
Tj (max)	175 °C
V _F (max)	0.75 V
trr (max)	35 ns

FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature

DESCRIPTION

The STTH302 which is using ST's new 200V planar technology, is specially suited for switching mode base drive & transistor circuits.

The device is also intended for use as a free wheeling diode in power supplies and other power switching applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	200	V
I _{F (AV)}	Average forward current	3	Α
I _{FSM}	Surge non repetitive forward current	130	A
T _{stg}	Storage temperature range	- 65 to + 175	°C
Tj	Maximum operating junction temperatu	175	°C

THERMAL PARAMETERS

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction-ambient*	25	°C/W

* On infinite heatsink with 10mm lead length.



STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Con	Min.	Тур.	Max.	Unit	
I _R *	Reverse leakage current	$T_j = 25^{\circ}C$	V _R = V _{RRM}			3	μA
		T _j = 125°C			4	75	
V _F **	Forward voltage drop	$T_j = 25^{\circ}C$	I _F = 3A			0.95	V
		T _j = 125°C			0.66	0.75	

Pulse test : * tp = 5 ms, δ < 2 %

** tp = 380 μ s, δ < 2 %

To evaluate the maximum conduction losses use the following equations:

 $P = 0.60 \text{ x } I_{F(AV)} + 0.05 I_{F}^{2}(RMS)$

DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit	
trr	Reverse recovery time	$I_F = 1A dI_F/dt = -50A/\mu s$ $V_R = 30V$	T _j = 25°C			35	ns
tfr	Forward recovery time	$I_F = 3A dI_F/dt = 50A/\mu s$ $V_{FR} = 1.1 x V_F max$	$T_j = 25^{\circ}C$		70		ns
V _{FP}	Forward recovery voltage		$T_j = 25^{\circ}C$		1.6		V

Fig. 1: Average forward power dissipation versus average forward current.



Fig. 3: Thermal resistance versus lead length.



Fig. 5: Forward voltage drop versus forward current.



Fig. 2: Average forward current versus ambient temperature (δ =0.5).



Fig. 4: Relative variation of thermal impedance junction ambient versus pulse duration (printed circuit board epoxy FR4, Lleads = 10mm).



Fig. 6: Junction capacitance versus reverse voltage applied (typical values).



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Fig. 7: Reverse recovery time versus dI_F/dt (90% confidence).

trr(ns) 100 90 80 70 60 Tj=125°C 50 ···· 40 25°C 30 · • • • 20 10 dlF/dt(A/µs) 0 10 100 1000 1

Fig. 9: Relative variations of dynamic parameters versus junction temperature.

IRM; trr; Qrr[Tj]/IRM; trr; Qrr[Tj=25°C] 5.0 IF=3A dIF/dt=200A/µs VR=100V _ 4.5 4.0 Qr 3.5 3.0 2.5 2.0 . . . 1.5 Tj(°C) 1.0 25 50 75 100 125 150 175 Fig. 8: Peak reverse recovery current versus dI_F/dt (90% confidence).



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PACKAGE MECHANICAL DATA

DO-201AD



		DIMEN	SIONS						
REF.	Millimeters		Inches		NOTES				
	Min.	Max.	Min.	Max.					
A		9.50		0.374	1 - The lead diameter \varnothing D is not controlled over zone E				
В	25.40		1.000						
ØC		5.30		0.209	2 - The minimum axial length within which the device may be				
ØD		1.30		0.051	1 placed with its leads bent at right angles is 0.59"(15 mm)				
E		1.25		0.049					

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH302	STTH302	DO-201AD	1.16 g	600	Ammopack
STTH302RL	STTH302	DO-201AD	1.16 g	1900	Tape and reel

White band indicates cathode

Epoxy meets UL94,V0

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